

Silicon PNP Power Transistors

2N6469

DESCRIPTION

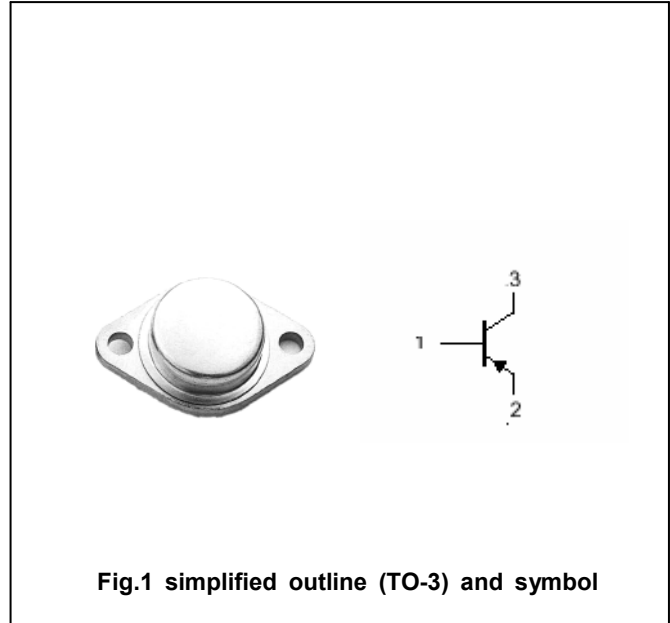
- With TO-3 package
- Low collector saturation voltage
- Excellent safe operating area
- High gain at high current

APPLICATIONS

- General-purpose of switching and linear-amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-50	V
V_{CEO}	Collector-emitter voltage	Open base	-40	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-15	A
I_B	Base current		-5	A
P_T	Total power dissipation	$T_C = 25 \square$	125	W
T_j	Junction temperature		200	\square
T_{stg}	Storage temperature		-65~200	\square

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-c}$	Thermal resistance junction to case	1.4	\square/W

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE0(SUS)}	Collector-emitter sustaining voltage	I _C =-0.2A ; I _B =0	-40			V
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =-5A ; I _B =-0.5A			-1.3	V
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =-15A ; I _B =-3A			-3.5	V
V _{BE}	Base-emitter on voltage	I _C =-15A ; V _{CE} =-4V			-3.5	V
I _{CEO}	Collector cut-off current	V _{CE} =-20V ; I _B =0			1.0	mA
I _{CEx}	Collector cut-off current	V _{CE} =-45V ; V _{BE} =-1.5V T _C =150°C			-0.2 -5.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V ; I _C =0			-5	mA
h _{FE-1}	DC current gain	I _C =-5A ; V _{CE} =-4V	20		150	
h _{FE-2}	DC current gain	I _C =-15A ; V _{CE} =-4V	5			
f _T	Transition frequency	I _C =-0.5A ; V _{CE} =-10V	4			MHz

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PACKAGE OUTLINE

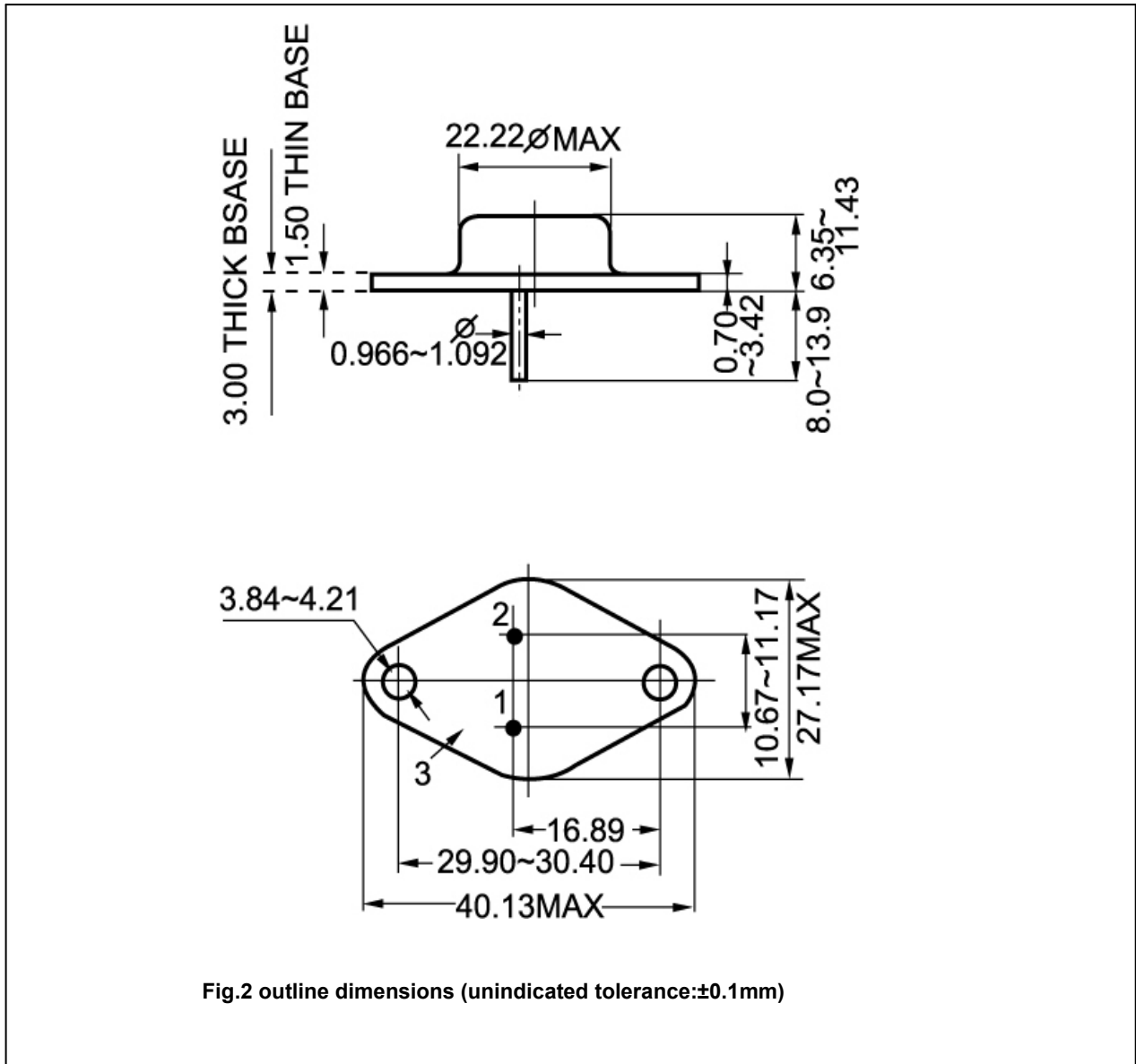


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)